

STX817

PNP MEDIUM POWER TRANSISTOR

Туре	Marking		
STX817	X817		

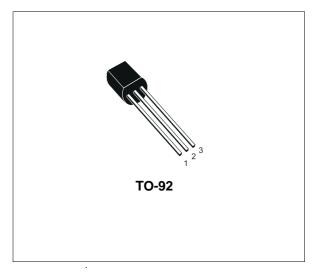
 DEVICE SUITABLE FOR THROUGH-HOLE PCB ASSEMBLY

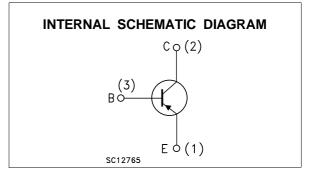
APPLICATIONS

- VOLTAGE REGULATION
- RELAY DRIVER
- GENERIC SWITCH

DECRIPTION

The STX817 is a PNP transistor manufactured using Planar Technology resulting in rugged high performance devices.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage $(I_E = 0)$	-120	V	
Vceo	Collector-Emitter Voltage (I _B = 0)	-80	V	
V_{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V	
Ιc	Collector Current	-1.5	А	
I _{CM}	Collector Peak Current (t _p < 5 ms)	-2	А	
Ι _Β	Base Current	-0.3	А	
Івм	Base Peak Current (t _p < 5 ms)	-0.6	А	
P _{tot}	Total Dissipation at $T_{amb} = 25 \ ^{\circ}C$	0.9	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	44.6	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	139	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

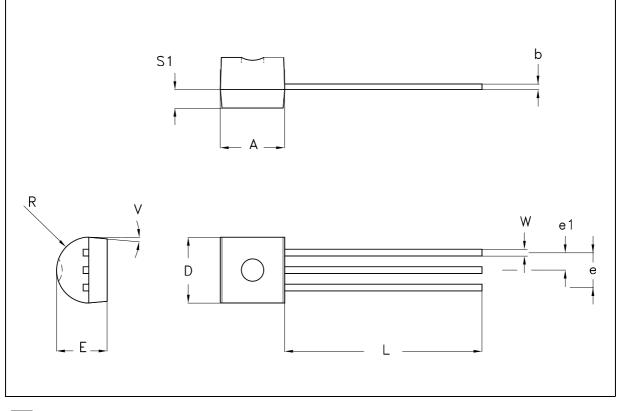
Symbol	Parameter	Test Co	onditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = -120 V				-500	μA
I _{CEO}	Collector Cut-off Current ($I_B = 0$)	V _{CE} = -80 V				-1	mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = -5 V				-100	μA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage $(I_B = 0)$	I _C = -10 mA		-80			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = -100 mA I _C = -1 A	I _B = -10 mA I _B = -100 mA			-0.25 -0.5	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = -100 mA I _C = -1 A	I _B = -10 mA I _B = -100 mA			-1 -1.1	V V
h _{FE} *	DC Current Gain	I _C = -100 mA I _C = -500 mA I _C = -1 A	V _{CE} = -2 V V _{CE} = -2 V V _{CE} = -2 V	140 80 40			
f⊤	Transition Frequency	I _C = -0.1 A	$V_{CE} = -10 V$		50		MHz

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

A7/

DIM.		mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.32		4.95	0.170		0.195	
b	0.36		0.51	0.014		0.020	
D	4.45		4.95	0.175		0.194	
E	3.30		3.94	0.130		0.155	
е	2.41		2.67	0.095		0.105	
e1	1.14		1.40	0.045		0.055	
L	12.70		15.49	0.500		0.609	
R	2.16		2.41	0.085		0.094	
S1	1.14		1.52	0.045		0.059	
W	0.41		0.56	0.016		0.022	
V	4 degree		6 degree	4 degree		6 degree	





\$7

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics. The ST logo is a trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco -Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

